TOSHIBA TC7SZ02AFE

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

# TC7SZ02AFE

# 2 INPUT NOR GATE

#### **FEATURES**

• High Output Drive : ± 24 mA (Typ.)

@VCC = 3V

Super High Speed Operation : tpD 2.4 ns (Typ.)

 $@V_{CC} = 5 \text{ V}, 50 \text{ pF}$ 

**Operation Voltage Range** :  $V_{CC(opr)} = 1.8 \sim 5.5 \text{ V}$ 

Supply Voltage Data Retention :  $V_{CC} = 1.5 \sim 5.5 \text{ V}$ 

Latch-up Performance

ESD Performance: Human Body Model > ±2000 V

Machine Model > ±200 V

Power Down Protection is provided on all inputs.

Matches the Performance of TC74LCX Series when

Operated at 3.3 V Vcc

Input Rise and Fall Time (tr, tf) (Recommended Operation Condition)

 $@V_{CC} = 1.8 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V} : 0 \sim 20 \text{ ns/V}$  $@V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ : 0~10 ns/V  $@V_{CC} = 5.5 V \pm 0.5 V$ : 0~5 ns/V

#### **MAXIMUM RATINGS** ( $Ta = 25^{\circ}C$ )

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CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	VCC	-0.5~6	V
DC Input Voltage	VIN	-0.5~6	V
DC Output Voltage	Vout	-0.5~V <sub>CC</sub> + 0.5	V
Input Diode Current	IK	± 20	mA
Output Diode Current	ГОК	± 20	mA
DC Output Current	IOUT	± 50	mA
DC V <sub>CC</sub> / Ground Current	ICC	± 50	mA
Power Dissipation	PD	150	mW
Storage Temperature	T <sub>stg</sub>	- 65~150	°C
Lead Temperature (10 s)	TL	260	°C

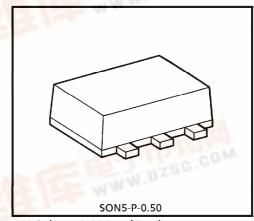
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Weight: 0.003 g (Typ.)

## DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC SYMBOL		тест	CONDITION		Ta = 25°C		Ta = −40~85°C		UNIT	
		TEST CONDITION		Vcc (V)	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
High-Level Input Voltage				1.8	0.75 × V <sub>CC</sub>		l	0.75 × V <sub>CC</sub>	I	V
				2.3 – 5.5	0.7 × V <sub>CC</sub>	_	-	0.7 × V <sub>CC</sub>	1	v
Low-Level Input				1.8	_	_	0.25 × V <sub>CC</sub>	_	0.25 × V <sub>CC</sub>	v
Voltage	VIL.			2.3 – 5.5	_	_	0.3 × V <sub>CC</sub>	_	0.3 × VCC	
				1.8	1.7	1.8	_	1.7	_	
High-Level			$I_{OH} = -100 \mu A$	2.3	2.2	2.3	_	2.2	_	
			$\frac{100 \mu }{\mu }$	3.0	2.9	3.0	_	2.9	_	
	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IL</sub>		4.5	4.4	4.5	_	4.4	_	- v
Output Voltage	VOH	VIIN — VIL	$I_{OH} = -8  \text{mA}$	2.3	1.9	2.15	_	1.9	_	
			$I_{OH} = -16  \text{mA}$	3.0	2.4	2.8	_	2.4	_	
			$I_{OH} = -24 \text{ mA}$	3.0	2.3	2.68	_	2.3	_	
			$I_{OH} = -32 \text{ mA}$	4.5	3.8	4.2	_	3.8	_	
			$I_{OL} = 100 \mu A$		_		0.1	_	0.1	
					_	0	0.1	_	0.1	
				0.1	_	0.1	] [			
Low-Level Output Voltage	Voi	$V_{IN} = V_{IH}$			_		0.1	_	0.1	- v
	VOL	or V <sub>IL</sub>	IOL = 8 mA	2.3	_	0.1	0.3	_	0.3	
			$I_{OL} = 16  \text{mA}$	3.0	_	0.15	0.4	_	0.4	
			$I_{OL} = 24  \text{mA}$	3.0	_	0.22	0.55	_	0.55	
			$I_{OL} = 32 \text{ mA}$	4.5	_	0.22	0.55	_	0.55	
Input Leakage Current	IN	V <sub>IN</sub> = 5.5 V or GND		0 – 5.5	_	_	± 1	_	± 10	μΑ
Quiescent Supply Current	lcc	V <sub>IN</sub> = V <sub>CC</sub> or GND		5.5	_	_	2	_	20	μΑ

# AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3 \text{ ns}$ )

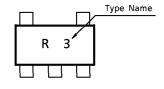
CHARACTERISTIC SYMBOL		TEST CONDITION (		Ta = 25°C			Ta = −40~85°C		UNIT	
CHARACTERISTIC	3 TIVIBOL	1E31 CONDITION	V <sub>CC</sub> (V)	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT	
Propagation tplH Delay Time tpHL			1.8	2.0	4.4	9.5	2.0	10.0		
		$C_L = 15  pF,$	2.5 ± 0.2	0.8	2.9	6.5	0.8	7.0		
	$R_L = 1 M\Omega$	3.3 ± 0.3	0.5	2.3	4.5	0.5	4.7			
		5.0 ± 0.5	0.5	1.9	3.9	0.5	4.1	ns		
		C <sub>L</sub> = 50 pF,	3.3 ± 0.3	1.5	2.9	5.0	1.5	5.2		
		$R_L = 500 \Omega$	5.0 ± 0.5	0.8	2.4	4.3	0.8	4.5		
Input Capacitance	CIN		0 - 5.5	_	4	_	_	_	рF	
Power Dissipation	C	er Dissipation (Not	(Note 1)	3.3		19	_	_	_	nE
Capacitance	C <sub>PD</sub>	(Note 1)	5.5	_	27	_	_	_	pF	

(Note 1): CpD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

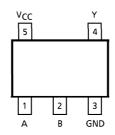
Average operating current can be obtained by the equation.

$$I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

### **MARKING**



## PIN ASSIGNMENT (TOP VIEW)



TRUTH TABLE

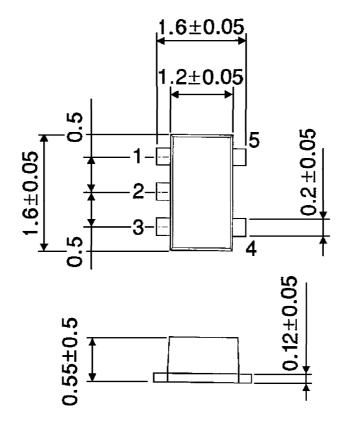
Α	В	Υ
L	L	Н
L	Н	L
Н	L	L
Н	Н	L

## **LOGIC DIAGRAM**



# PACKAGE DIMENSIONS SON5-P-0.50

Unit: mm



Weight: 0.003 g (Typ.)